

isc Silicon NPN Power Transistor

2SC5548A

DESCRIPTION

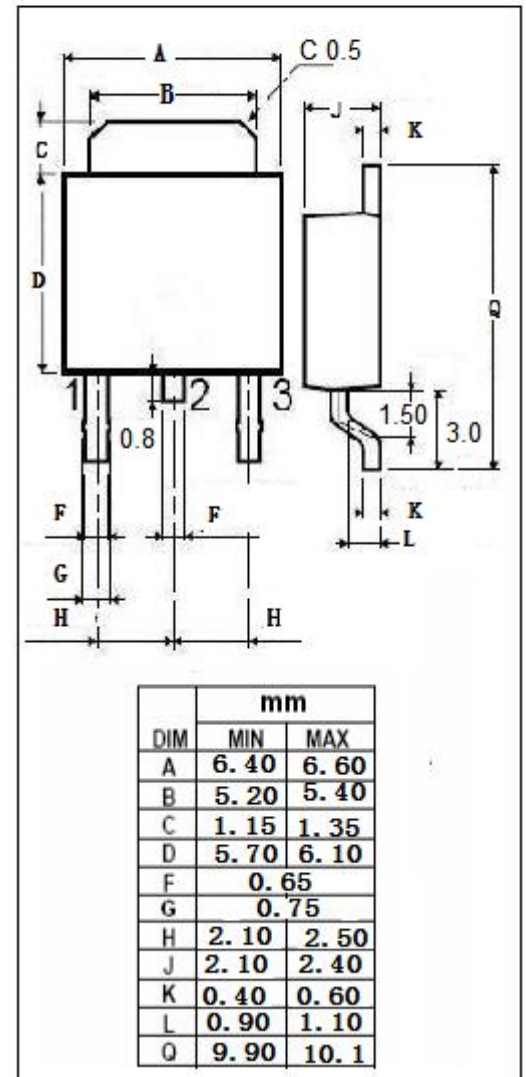
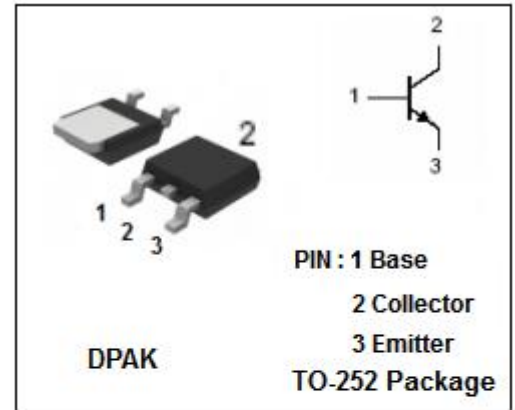
- With TO-252(DPAK) packaging
- Excellent linearity of h_{FE}
- Low collector-to-emitter saturation voltage
- Fast switching speed
- Complementary to 2SB1204
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Relay drivers, high-speed inverters , converters and Other general high current switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	600	V
V_{CEO}	Collector-Emmitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_c	Collector Current-Continuous	2	A
P_c	Collector Power Dissipation	1	W
	Collector Power Dissipation @ $T_c=25^{\circ}C$	15	
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor

2SC5548A

ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =1mA; I _B =0	600			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =10mA; I _B =0	400			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 0.8A; I _B = 0.1A			1.0	mV
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 0.8A; I _B = 0.1A			1.3	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 480V; I _E = 0			20	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7V; I _C =0			10	μ A
h _{FE-1}	DC Current Gain	I _C = 1mA ; V _{CE} = 5V	20			
h _{FE-2}	DC Current Gain	I _C = 0.2A ; V _{CE} = 5V	40		100	